CMPT4033

SURFACE MOUNT
PNP SILICON TRANSISTOR



SOT-23 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT4033 type is a PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for very high current, general purpose amplifier applications.

MARKING CODE: C4A

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	500	mA
Peak Collector Current	I_{CM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

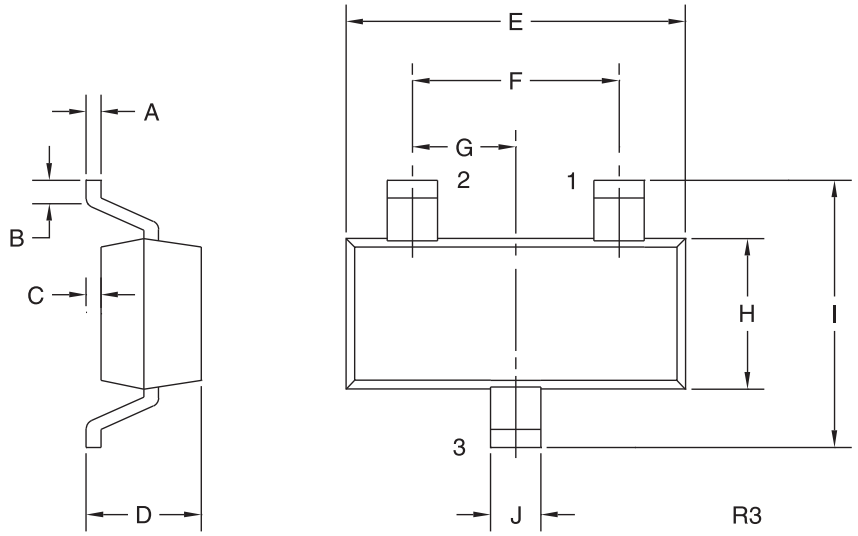
SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=60V		50	nA
I_{EBO}	V_{EB}=5.0V		10	nA
BV_{CBO}	I_C=10μA	80		V
BV_{CEO}	I_C=10mA	80		V
BV_{EBO}	I_E=10μA	5.0		V
$V_{CE(SAT)}$	I_C=150mA, I_B=15mA		0.15	V
$V_{CE(SAT)}$	I_C=500mA, I_B=50mA		0.50	V
$V_{BE(SAT)}$	I_C=150mA, I_B=15mA		0.90	V
$V_{BE(SAT)}$	I_C=500mA, I_B=50mA		1.10	V
h_{FE}	V_{CE}=5.0V, I_C=0.1mA	75		
h_{FE}	V_{CE}=5.0V, I_C=100mA	100	300	
h_{FE}	V_{CE}=5.0V, I_C=500mA	70		
f_T	V_{CE}=10V, I_C=50mA, f=1.0MHz	100		MHz
C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz		20	pF
C_{ib}	V_{EB}=0.5V, I_C=0, f=1.0MHz		110	pF

R5 (1-February 2010)

CMPT4033

SURFACE MOUNT
PNP SILICON TRANSISTOR

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:
1) Base
2) Emitter
3) Collector

MARKING CODE: C4A

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)